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**Large electric-field control of perpendicular magnetic anisotropy in strained [Co/Ni] / PZT heterostructures** DANIEL GOPMAN, CINDI DENNIS, P. J. CHEN, NIST - Natl Inst of Stds Tech, YURY IUNIN, Institute of Solid State Physics, Russian Academy of Sciences, Chernogolovka, Moscow Region, Russia, ROBERT SHULL, NIST - Natl Inst of Stds Tech — We present a piezoelectric/ferromagnetic heterostructure with PMA - a Co/Ni multilayer sputtered directly onto a Pb(Zr,Ti)O<sub>3</sub> (PZT) substrate. Chemical-mechanical polishing was used to reduce the roughness of PZT plates to below 2 nm *rms*, enabling optimal magnetoelectric coupling via the direct interface between PZT and sputtered Co/Ni films with large PMA ( $K_{\text{eff}} = (95 \pm 9 \text{ kJ/m}^3)$ ). We grew the following layer stack: Ta(3)/Pt(2)/[Co(0.15)/Ni(0.6)]<sub>x4</sub>/Co(0.15)/Pt(2)/Ta(3); numbers in parentheses indicate thicknesses in nm. Applied electric fields up to +/- 2 MV/m to the PZT generated 0.05% in-plane compression in the Co/Ni multilayer, enabling a large electric-field reduction of the PMA ( $\Delta K_{\text{eff}} \geq 10^3 \text{ J/m}^3$ ) and of the coercive field (35%). Our results demonstrate that: (i) heterostructures combining PZT and [Co/Ni] exhibit larger PMA ( $K_{\text{eff}} \sim 10^5 \text{ J/m}^3$ ) than previous magnetoelectric heterostructures based on Co/Pt and CoFeB, enabling thermally stable hybrid magnetoelectric/spintronic devices only tens of nm in diameter and (ii) electric-field control of the PMA is promising for more energy efficient switching of spintronic devices.

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